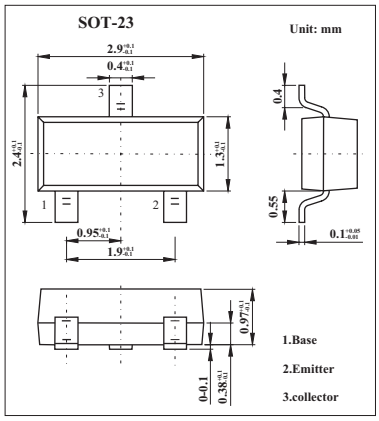
Silicon NPN Epitaxial

2SC3265



■ Features

- High DC current gain: h_{FE} (1) = 100320.
- Low saturation voltage: $V_{CE\ (sat)}$ = 0.4 V (max) (I_C = 500 mA, I_B = 20 mA).

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	800	mA
Base current	I_B	160	mA
Collector power dissipation	P_C	200	mW
Junction temperature	Tj	150	℃
Storage temperature range	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 30 V, I_E = 0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 50 V, IC = 0			0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)\ CEO}$	I_C = 10 mA, I_B = 0	25			V
Emitter-base breakdown voltage	$V_{(BR)\ EBO}$	I_E = 0.1 mA, I_C = 0	5			V
DC current gain	h_{FE}	V_{CE} = 1 V, I_C = 100 mA	100		320	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 500 mA, I_B = 20 mA			0.4	V
Base-emitter voltage	V_{BE}	V_{CE} = 1 V, I_C = 10 mA	0.5		0.8	V
Transition frequency	f_T	V_{CE} = 5 V, I_C = 10 mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz		13		pF

■ h_{FE} Classification

Marking	EO	EY
hFE	100～200	160～320